

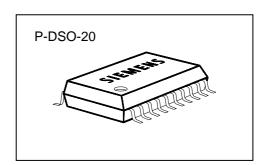
Smart Four Channel Highside Power Switch

Features

- Overload protection
- Current limitation
- Short-circuit protection
- Thermal shutdown
- Overvoltage protection (including load dump)
- Fast demagnetization of inductive loads
- Reverse battery protection¹⁾
- Undervoltage and overvoltage shutdown with auto-restart and hysteresis
- Open drain diagnostic output
- Open load detection in OFF-state
- CMOS compatible input
- Loss of ground and loss of V_{bb} protection
- Electrostatic discharge (ESD) protection

Product Summary

Overvoltage Protection	$V_{\rm bb(AZ)}$)	43	V
Operating voltage				V
active channels:	one	two parallel	four parallel	
On-state resistance RON	200	100	50	$m\Omega$
Nominal load current I _{L(NOM)}	1.9	2.8	4.4	Α
Current limitation I _{L(SCr)}	4	4	4	Α



Application

- μC compatible power switch with diagnostic feedback for 12 V and 24 V DC grounded loads
- All types of resistive, inductive and capacitive loads
- Replaces electromechanical relays and discrete circuits

General Description

N channel vertical power FET with charge pump, ground referenced CMOS compatible input and diagnostic feedback, monolithically integrated in Smart SIPMOS® technology.

Providing embedded protective functions.

Pin Definitions and Functions

Pin	Symbol	Function
1,10,	V_{bb}	Positive power supply voltage. Design the
11,12,		wiring for the simultaneous max. short circuit
15,16,		currents from channel 1 to 4 and also for low
19,20		thermal resistance
3	IN1	Input 1 4, activates channel 1 4 in case of
5	IN2	logic high signal
7	IN3	
9	IN4	
18	OUT1	Output 1 4, protected high-side power output
17	OUT2	of channel 1 4. Design the wiring for the
14	OUT3	max. short circuit current
13	OUT4	
4	ST1/2	Diagnostic feedback 1/2 of channel 1 and
		channel 2, open drain, low on failure
8	ST3/4	Diagnostic feedback 3/4 of channel 3 and
		channel 4, open drain, low on failure
2	GND1/2	Ground 1/2 of chip 1 (channel 1 and channel 2)
6	GND3/4	Ground 3/4 of chip 2 (channel 3 and channel 4)

Pin configuration (top view)

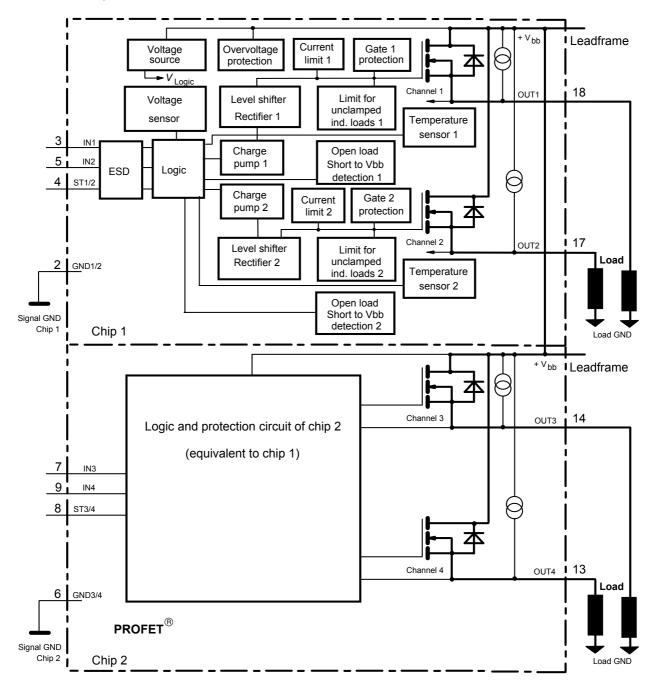
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V_{bb}	1	•	20	V_{bb}
GND1/2	2		19	V_{bb}
IN1	3		18	OUT1
ST1/2	4		17	OUT2
IN2	5		16	V_{bb}
GND3/4	6		15	V_{bb}
IN3	7		14	OUT3
ST3/4	8		13	OUT4
IN4	9		12	V_{bb}
V_{bb}	10		11	V _{bb}

With external current limit (e.g. resistor R_{GND} =150 Ω) in GND connection, resistor in series with ST connection, reverse load current limited by connected load.



Block diagram

Four Channels; Open Load detection in off state;



Leadframe connected to pin 1, 10, 11, 12, 15, 16, 19, 20



Maximum Ratings at $T_j = 25$ °C unless otherwise specified

Parameter		Symbol	Values	Unit
Supply voltage (overvoltage prote	Supply voltage (overvoltage protection see page 4)			V
Supply voltage for full short circuity, $T_{j,\text{start}} = -40 \dots + 150^{\circ}\text{C}$	t protection	V _{bb}	34	V
Load current (Short-circuit curren	t, see page 5)	<i>I</i> L	self-limited	Α
Load dump protection ²⁾ V_{LoadDump} $R_{\text{I}^{3)}} = 2 \Omega$, $t_{\text{d}} = 200 \text{ ms}$; IN = low ceach channel loaded with $R_{\text{L}} = 7$	or high,	V _{Load} dump ⁴⁾	60	V
Operating temperature range		T _j	-40+150	°C
Storage temperature range		$T_{ m stg}$	-55+150	
Power dissipation (DC) ⁵	$T_{\rm a} = 25^{\circ}{\rm C}$:	P _{tot}	3.6	W
(all channels active)	$T_{\rm a} = 85^{\circ}{\rm C}$:		1.9	
Inductive load switch-off energy of $V_{bb} = 12V$, $T_{j,start} = 150^{\circ}C^{5}$,	lissipation, single pulse			
$I_{L} = 1.9 \text{ A}, Z_{L} = 66 \text{ mH}, 0 \Omega$	one channel:	<i>E</i> _{AS}	150	mJ
$I_{L} = 2.8 \text{ A}, Z_{L} = 66 \text{ mH}, 0 \Omega$	two parallel channels:		320	
$I_{L} = 4.4 \text{ A}, Z_{L} = 66 \text{ mH}, 0 \Omega$	four parallel channels:		800	
see diagrams on page 9				
Electrostatic discharge capability (Human Body Model)	(ESD)	V _{ESD}	1.0	kV
Input voltage (DC)		V _{IN}	-10 +16	V
Current through input pin (DC)		I _{IN}	±2.0	mA
Current through status pin (DC)		I ST	±5.0	
see internal circuit diagram page 8				
Thermal resistance				
junction - soldering point ^{5),6)}	each channel:	R _{this}	16	K/W
junction - ambient ⁵⁾	one channel active:	R_{thja}	44	
-	all channels active:	'	35	

Semiconductor Group

Supply voltages higher than $V_{bb(AZ)}$ require an external current limit for the GND and status pins, e.g. with a 150 Ω resistor in the GND connection and a 15 k Ω resistor in series with the status pin. A resistor for input protection is integrated.

 $^{^{3)}}$ R_{I} = internal resistance of the load dump test pulse generator

 $^{^{4)}}$ $V_{Load\ dump}$ is setup without the DUT connected to the generator per ISO 7637-1 and DIN 40839

Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70μm thick) copper area for V_{bb} connection. PCB is vertical without blown air. See page 14

⁶⁾ Soldering point: upper side of solder edge of device pin 15. See page 14



Electrical Characteristics

Parameter and Conditions, each of the four channels		Symbol		Values		
at T _j = 25 °C, V_{bb} = 12 V unless of	otherwise specified		min	typ	max	
Load Switching Capabiliti	es and Characteristics	3				
On-state resistance (V _{bb} to	OUT)					
$I_L = 1.8 A$ each	channel, $T_j = 25$ °C:	Ron		165	200	mΩ
	$T_{\rm j} = 150^{\circ}{\rm C}$:			320	400	
two paralle	el channels, $T_j = 25$ °C:			83	100	
four paralle	el channels, $T_j = 25^{\circ}\text{C}$:			42	50	
Nominal load current	one channel active:	I _{L(NOM)}	1.7	1.9		Α
two p	arallel channels active:		2.6	2.8		
four p	arallel channels active:		4.1	4.4		
Device on PCB ⁵), $T_a = 85^\circ$	C, <i>T</i> _j ≤ 150°C					
Output current while GND oup; V _{bb} = 30 V, V _{IN} = 0, se	•	I _{L(GNDhigh)}			10	mA
Turn-on time	to 90% V _{OUT} :	<i>t</i> on	80	200	400	μs
Turn-off time	to 10% V _{OUT} :	$t_{ m off}$	80	200	400	•
$R_{\rm L} = 12 \Omega, T_{\rm j} = -40+150^{\circ}$						
Slew rate on		d V/dt _{on}	0.1		1	V/µs
10 to 30% V_{OUT} , $R_L = 12 \Omega$	T_{j} =-40+150°C:					
Slew rate off 70 to 40% V_{OUT} , $R_{\text{L}} = 12 \Omega$		-d V/dt _{off}	0.1		1	V/µs
Operating Parameters						
Operating voltage ⁷⁾	<i>T</i> _j =-40+150°C:	V _{bb(on)}	5.0		34	V
Undervoltage shutdown	T _j =-40+150°C:	V _{bb(under)}	3.5		5.0	V
						ĭ

Operating randineters						
Operating voltage ⁷⁾	<i>T</i> _j =-40+150°C:	$V_{\rm bb(on)}$	5.0		34	V
Undervoltage shutdown	$T_{\rm j}$ =-40+150°C:	V _{bb(under)}	3.5		5.0	V
Undervoltage restart	<i>T</i> _j =-40+25°C:	V _{bb(u rst)}			5.0	V
	$T_{\rm j} = +150^{\circ}{\rm C}$:				7.0	
Undervoltage restart of charge page 14	oump $T_j = -40+150$ °C:	V _{bb(ucp)}	-	5.6	7.0	V
Undervoltage hysteresis $\Delta V_{bb(under)} = V_{bb(u rst)} - V_{bb(under)}$		$\Delta V_{ m bb(under)}$	-	0.2		V
Overvoltage shutdown	$T_{\rm j}$ =-40+150°C:	$V_{\rm bb(over)}$	34		43	V
Overvoltage restart	$T_{\rm j}$ =-40+150°C:	V _{bb(o rst)}	33			V
Overvoltage hysteresis	$T_{\rm j}$ =-40+150°C:	$\Delta V_{ m bb(over)}$		0.5		V
Overvoltage protection ⁸⁾ $I_{bb} = 40 \text{ mA}$	<i>T</i> _j =-40+150°C:	$V_{\mathrm{bb}(AZ)}$	42	47		V

⁷⁾ At supply voltage increase up to V_{bb} = 5.6 V typ without charge pump, $V_{OUT} \approx V_{bb}$ - 2 V

 $^{^{8)}}$ see also $V_{\rm ON(CL)}$ in circuit diagram on page 8.



BTS712N1

Parameter and Conditions, each of the four channels		Symbol		Values		Unit
at $T_j = 25$ °C, $V_{bb} = 12$ V unless otherwise specified			min	typ	max	•
Standby current, all channels off 7	i =25°C:	I _{bb(off)}		180	300	μΑ
•	=150°C:	55(611)		160	300	•
Operating current 9, $V_{IN} = 5V$, $T_i = -40+15$	50°C					
$I_{\text{GND}} = I_{\text{GND1/2}} + I_{\text{GND3/4}},$ one cha	nnel on:	<i>I</i> _{GND}		0.35	0.8	mΑ
four chan	nels on:			1.2	2.8	
Protection Functions ¹⁰⁾						
Initial peak short circuit current limit, (see tir	ning					
diagrams, page 11) each channel, T_j	=-40°C:	I _{L(SCp)}	5.5	9.5	13	Α
T	j =25°C:		4.5	7.5	11	
$T_{j} = 0$	+150°C:		2.5	4.5	7	
two parallel c	hannels	twice	the curre	nt of one	channel	
four parallel c	hannels	four times	the curre	nt of one	channel	
Repetitive short circuit current limit,						
$T_{\rm j} = T_{\rm jt}$ each	channel	I _{L(SCr)}		4		Α
two parallel c	hannels			4		
four parallel c	hannels			4		
(see timing diagrams, page 11)						
2.	=-40°C:	$t_{ m off(SC)}$		5.5		ms
$ au_{j,start}$	= 25°C:			4		
(see page 10 and timing diagrams on page 11)						
Output clamp (inductive load switch off) ¹¹⁾ at $V_{ON(CL)} = V_{bb} - V_{OUT}$		$V_{ON(CL)}$	1	47		V
Thermal overload trip temperature		T_{jt}	150			°C
Thermal hysteresis		ΔT_{jt}		10		K
Reverse Battery						
Reverse battery voltage 12)		- V _{bb}			32	V
Drain-source diode voltage ($V_{out} > V_{bb}$) $I_L = -1.9 \text{ A}, T_j = +150 ^{\circ}\text{C}$		-V _{ON}		610		mV
Diagnostic Characteristics						
Open load detection current		$I_{L(off)}$		30		μΑ
Open load detection voltage $T_j = -40$	+150°C:	$V_{\rm OUT(OL)}$	2	3	4	V

⁹⁾ Add I_{ST} , if $I_{ST} > 0$

¹⁰⁾ Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

¹¹⁾ If channels are connected in parallel, output clamp is usually accomplished by the channel with the lowest VON(CL)

Requires a 150 Ω resistor in GND connection. The reverse load current through the intrinsic drain-source diode has to be limited by the connected load. Note that the power dissipation is higher compared to normal operating conditions due to the voltage drop across the intrinsic drain-source diode. The temperature protection is not active during reverse current operation! Input and Status currents have to be limited (see max. ratings page 3 and circuit page 8).

BTS712N1

Parameter and Conditions, each of the four channels	Symbol		Values	i	Unit	
at T _j = 25 °C, V_{bb} = 12 V unless otherwise specified		min	typ	max		
Input and Status Feedback ¹³⁾						
Input resistance (see circuit page 8) $T_j = -40+150$ °C	: R _I	2.5	3.5	6	kΩ	
Input turn-on threshold voltage $T_j = -40+150$ °C	: V _{IN(T+)}	1.7		3.5	V	
Input turn-off threshold voltage $T_j = -40+150$ °C	: V _{IN(T-)}	1.5			V	
Input threshold hysteresis	$\Delta V_{\text{IN(T)}}$		0.5		V	
Off state input current $V_{IN} = 0.4 \text{ V}$ $T_j = -40+150$ °C:	: I _{N(off)}	1		50	μΑ	
On state input current $V_{IN} = 5 \text{ V}$ $T_j = -40+150$ °C:	:	20	50	90	μΑ	
Delay time for status with open load (see timing diagrams, page 12)	$t_{ m d(ST~OL3)}$		220		μs	
Status output (open drain)						
Zener limit voltage $T_j = -40 + 150$ °C, $I_{ST} = +1.6$ mA	: V _{ST(high)}	5.4	6.1		V	
ST low voltage $T_{j} = -40 + 25$ °C, $I_{ST} = +1.6$ mA	: V _{ST(low)}			0.4		
$T_{\rm j}$ = +150°C, $I_{\rm ST}$ = +1.6 mA	:			0.6		

 $^{^{\}rm 13)}\,$ If ground resistors ${\rm R}_{\rm GND}$ are used, add the voltage drop across these resistors.



Truth Table

Channel 1 and 2	Chip 1	IN1	IN2	OUT1	OUT2	ST1/2	ST1/2
Channel 3 and 4	Chip 2	IN3	IN4	OUT3	OUT4	ST3/4	ST3/4
(equivalent to channel 1 and	2)						
						BTS 711L1	BTS 712N1
Normal operation		L	L	L	L	Н	Н
		L	Н	L	Н	Н	Н
		Н	L	Н	L	Н	Н
		Н	Н	Н	Н	Н	Н
Open load	Channel 1 (3)	L	L	Z	L	H(L ¹⁴⁾)	L
		L	Н	Z	Н	Н	Н
		Н	Х	Н	Х	L	Н
	Channel 2 (4)	L	L	L	Z	H(L ¹⁴⁾)	L
		Н	L	Н	Z	Н	Н
		X	Н	X	Н	L	Н
Short circuit to Vbb	Channel 1 (3)	L	L	Н	L	L ¹⁵)	L ¹⁵⁾
		L	Н	Н	Н	Н	Н
		Н	Х	Н	Х	H(L ¹⁶⁾)	Н
	Channel 2 (4)	L	L	L	Н	Ĺ15)	L ¹⁵)
		Н	L	Н	Н	H .	Н
		X	Н	X	Н	H(L ¹⁶⁾)	Н
Overtemperature	both channel	L	L	L	L	Н	Н
		Х	Н	L	L	L	L
		Н	X	L	L	L	L
	Channel 1 (3)	L	Х	L	Х	Н	Н
		Н	Х	L	Х	L	L
	Channel 2 (4)	Х	L	Х	L	Н	Н
		Х	Н	Х	L	L	L
Undervoltage/ Overvoltage		Х	X	L	L	Н	Н

L = "Low" Level

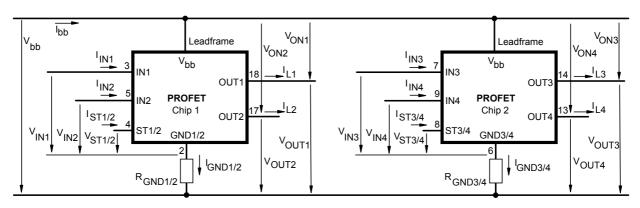
X = don't care

Z = high impedance, potential depends on external circuit

H = "High" Level Status signal valid after the time delay shown in the timing diagrams

Parallel switching of channel 1 and 2 (also channel 3 and 4) is easily possible by connecting the inputs and outputs in parallel (see truth table). If switching channel 1 to 4 in parallel, the status outputs ST1/2 and ST3/4 have to be configured as a 'Wired OR' function with a single pull-up resistor.

Terms



Leadframe (V_{bb}) is connected to pin 1,10,11,12,15,16,19,20

External R_{GND} optional; two resistors R_{GND1/2} ,R_{GND3/4} = 150 Ω or a single resistor R_{GND} = 75 Ω for reverse battery protection up to the max. operating voltage.

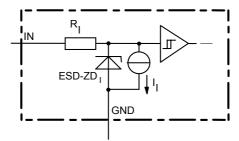
¹⁴⁾ With additional external pull up resistor

An external short of output to V_{bb} in the off state causes an internal current from output to ground. If R_{GND} is used, an offset voltage at the GND and ST pins will occur and the $V_{ST low}$ signal may be errorious.

¹⁶⁾ Low resistance to $V_{\rm bb}$ may be detected by no-load-detection

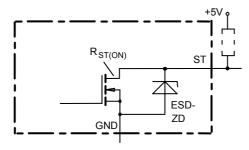


Input circuit (ESD protection), IN1...4



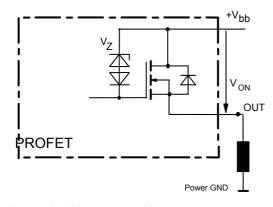
ESD zener diodes are not to be used as voltage clamp at DC conditions. Operation in this mode may result in a drift of the zener voltage (increase of up to 1 V).

Status output, ST1/2 or ST3/4



ESD-Zener diode: 6.1 V typ., max 5.0 mA; $R_{ST(ON)}$ < 380 Ω at 1.6 mA, ESD zener diodes are not to be used as voltage clamp at DC conditions. Operation in this mode may result in a drift of the zener voltage (increase of up to 1 V).

Inductive and overvoltage output clamp, OUT1...4



 V_{ON} clamped to $V_{ON(CL)} = 47 \text{ V typ.}$

Overvoltage protection of logic part GND1/2 or GND3/4

+ V_{bb}

Logic

R_{ST}

ST

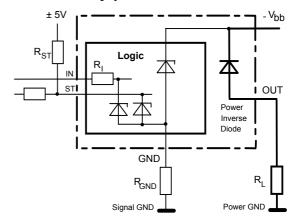
V_{Z2}

GND

R_{GND}

 V_{Z1} = 6.1 V typ., V_{Z2} = 47 V typ., R_{I} = 3.5 k Ω typ., R_{GND} = 150 Ω

Reverse battery protection



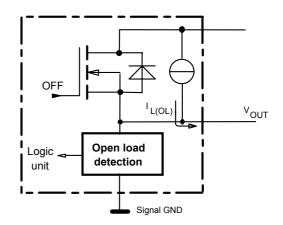
 $R_{GND} = 150 \Omega$, $R_{I} = 3.5 k\Omega$ typ,

Temperature protection is not active during inverse current operation.

Open-load detection, OUT1...4

OFF-state diagnostic condition:

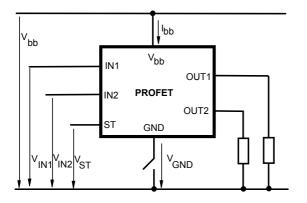
 $V_{OUT} > 3 \text{ V typ.}$; IN low





GND disconnect

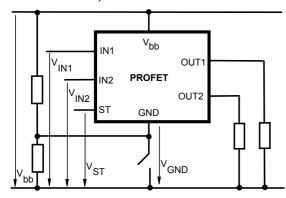
(channel 1/2 or 3/4)



Any kind of load. In case of IN=high is $VOUT \approx VIN - VIN(T+)$. Due to VGND > 0, no VST = low signal available.

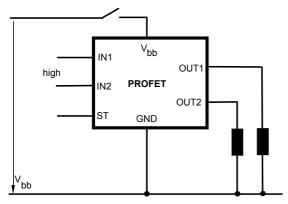
GND disconnect with GND pull up

(channel 1/2 or 3/4)



Any kind of load. If $V_{GND} > V_{IN} - V_{IN(T+)}$ device stays off Due to $V_{GND} > 0$, no $V_{ST} = low$ signal available.

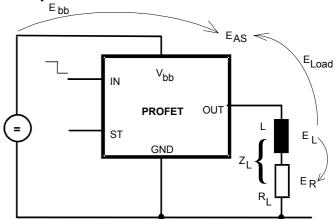
V_{bb} disconnect with energized inductive load



For an inductive load current up to the limit defined by E_{AS} (max. ratings see page 3 and diagram on page 9) each switch is protected against loss of V_{bb} .

Consider at your PCB layout that in the case of Vbb disconnection with energized inductive load the whole load current flows through the GND connection.

Inductive load switch-off energy dissipation



Energy stored in load inductance:

$$E_L = \frac{1}{2} \cdot L \cdot I_1^2$$

While demagnetizing load inductance, the energy dissipated in PROFET is

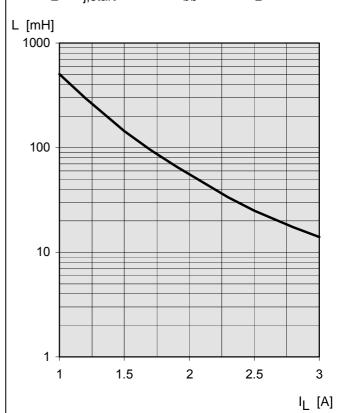
$$E_{AS} = E_{bb} + E_L - E_R = V_{ON(CL)} \cdot i_L(t) dt$$

with an approximate solution for $R_L > 0 \Omega$:

$$E_{AS} = \frac{I_L \cdot L}{2 \cdot R_L} (V_{bb} + |V_{OUT(CL)}|) ln (1 + \frac{I_L \cdot R_L}{|V_{OUT(CL)}|})$$

Maximum allowable load inductance for a single switch off (one channel)⁵⁾

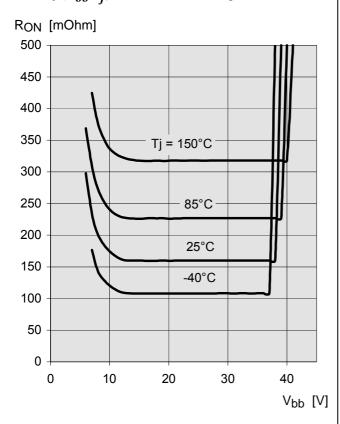
$$L = f(I_L)$$
; T_{j,start} = 150°C, V_{bb} = 12 V, R_L = 0 Ω





Typ. on-state resistance

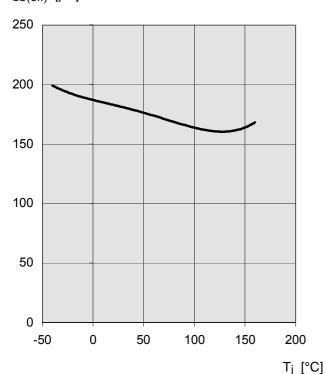
 $R_{ON} = f(V_{bb}, T_i)$; IL = 1.8 A, IN = high



Typ. standby current

 $I_{bb(off)} = f(T_i)$; $V_{bb} = 9...34 \text{ V}$, IN1...4 = low

I_{bb}(off) [μA]

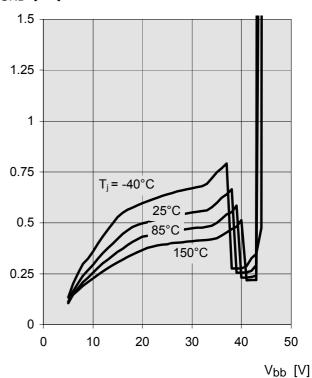


lbb(off) includes four times the current lL(off) of the open load detection current sources.

Typ. ground pin operating current

 $I_{GND} = f(V_{bb}, T_j); V_{IN} = \text{high (one channel on)}$

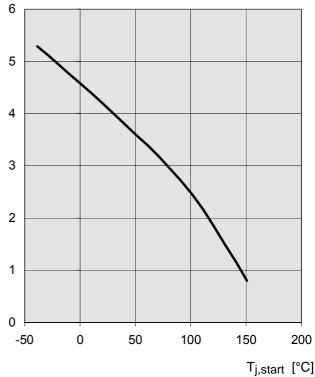
IGND [mA]



Typ. initial short circuit shutdown time

 $t_{off(SC)} = f(T_{j,start}); \ \forall_{bb} = 12 \ \forall$

 $t_{\text{Off}(SC)} \ [\text{msec}]$





Timing diagrams

Timing diagrams are shown for chip 1 (channel 1/2). For chip 2 (channel 3/4) the diagrams are valid too. The channels 1 and 2, respectively 3 and 4, are symmetric and consequently the diagrams are valid for each channel as well as for permuted channels

Figure 1a: V_{bb} turn on:

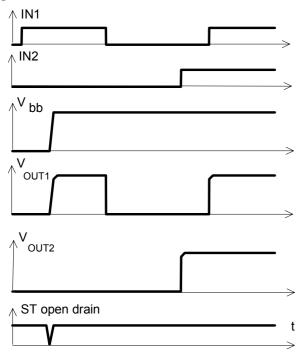
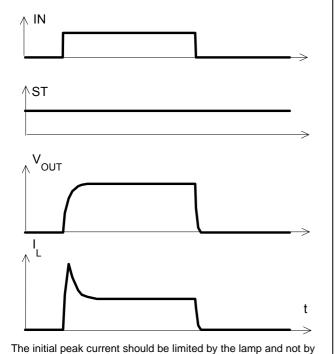


Figure 2a: Switching a lamp:



the initial short circuit current $I_{L(SCp)} = 7.5$ A typ. of the device.

Figure 2b: Switching an inductive load,

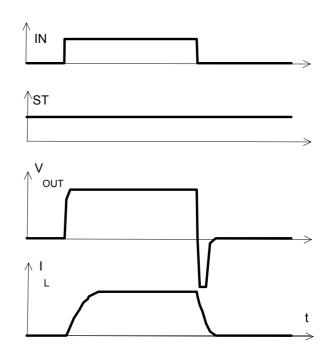
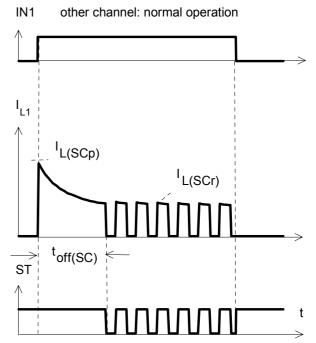


Figure 3a: Turn on into short circuit: shut down by overtemperature, restart by cooling



Heating up of the chip may require several milliseconds, depending on external conditions ($t_{off(SC)}$ vs. $T_{j,start}$ see page 11)

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Figure 3b: Turn on into short circuit: shut down by overtemperature, restart by cooling (two parallel switched channels 1 and 2)

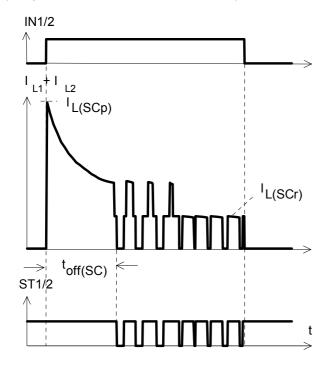


Figure 4a: Overtemperature: Reset if $T_j < T_{jt}$

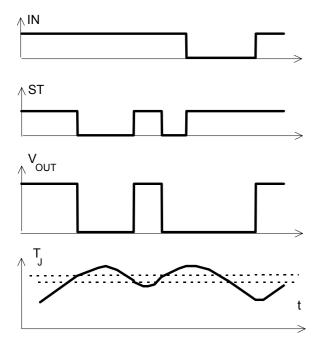
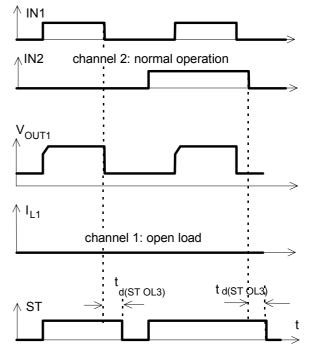


Figure 5a: Open load: detection in OFF-state, turn on/off to open load



 $t_{\text{d}(\text{ST},\text{OL3})}$ depends on external circuitry because of high impedance

*) $I_L = 30 \,\mu\text{A typ}$

Figure 6a: Undervoltage:

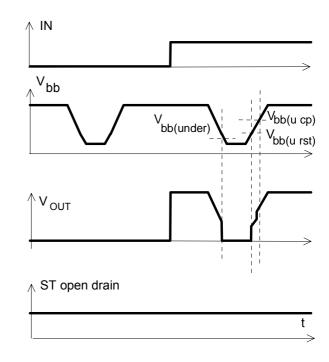
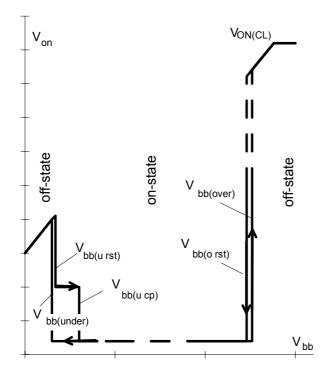


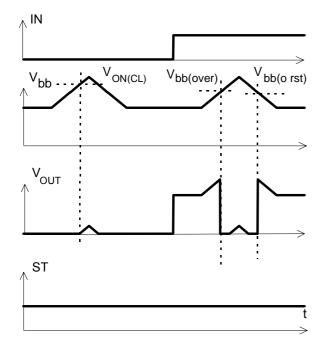


Figure 6b: Undervoltage restart of charge pump



IN = high, normal load conditions. Charge pump starts at $V_{bb(ucp)}$ = 5.6 V typ.

Figure 7a: Overvoltage:





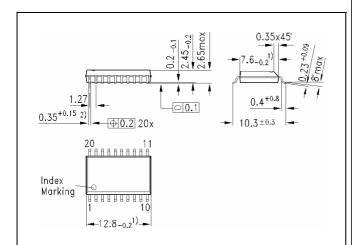
Package and Ordering Code

Standard P-DSO-20-9

Ordering Code

BTS712N1

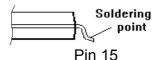
Q67060-S7001-A2



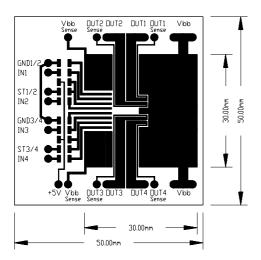
All dimensions in millimetres

- 1) Does not include plastic or metal protrusions of 0.15 max per side
- 2) Does not include dambar protrusion of 0.05 max per side

Definition of soldering point with temperature T_s: upper side of solder edge of device pin 15.



Printed circuit board (FR4, 1.5mm thick, one layer $70\mu m$, $6cm^2$ active heatsink area) as a reference for max. power dissipation P_{tot} , nominal load current $I_{L(NOM)}$ and thermal resistance R_{thia}



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